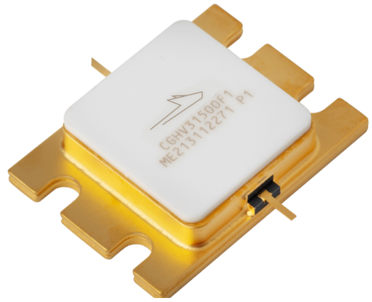
CGHV31500F1

2.7 – 3.1 GHz, 500 W GaN HEMT



Package Type: 440226
PN: CGHV31500F1

Description

Wolfspeed’s CGHV31500F1 is a gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically with high efficiency and high gain for the 2.7 - 3.1 GHz S-Band radar band. The device has been developed with long pulse capability to meet the developing trends in radar architectures. The transistor is matched to 50-ohms on the input and 50-ohms on the output. The CGHV31500F1 is based on Wolfspeed’s high power density 50 V, 0.4 µm GaN on Silicon Carbide (SiC) manufacturing process. The transistor is supplied in a ceramic/metal flange package.

Features

- P_{SAT}: 500W
- DE: >65%
- LSG: 13 dB

Note: Features are typical performance across frequency under 25°C operation. Please reference performance charts for additional details.

Applications

- Civil and Military Pulsed Radar Amplifiers

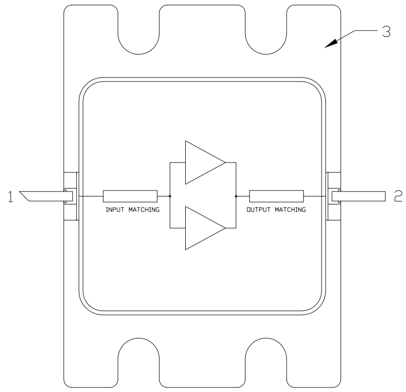


Figure 1: Functional Block Diagram

RoHS compliant

4600 Silicon Drive | Durham, NC 27703 | Tel: +1.919.313.5300

Absolute Maximum Ratings

Parameter	Symbol	Rating	Units	Conditions
Drain Voltage	V_D	50	V	25°C
Gate Voltage	V_G	-10, +2		
Drain Current	I_D	24	A	
Gate Current	I_G	80	mA	25°C
Input Power	P_{IN}	48	dBm	
Dissipated Power	P_{DISS}	418	W	85°C
Storage Temperature	T_{STG}	-55, +150		
Mounting Temperature	T_J	320	°C	30 seconds
Junction Temperature		225		MTTF > 1e6 Hours
Output Mismatch Stress	VSWR	5:1	Ψ	
PulseWidth	PW	2000	µs	
Duty Cycle	DC	20	%	

Recommended Operating Conditions

Parameter	Symbol	Rating	Units	Conditions
Drain Voltage	V_D	50	V	
Gate Voltage	V_G	-2.7		
Drain Current	I_{DQ}	500	mA	
Input Power	P_{IN}	46	dBm	
Case Temperature	T_{CASE}	-40 to 75	°C	2mS, DC = 20%

RF Specifications

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 2000 µs, DC = 20%, T_{BASE} = +25 °C

Parameter	Units	Frequency	Min	Typical	Max	Conditions
Frequency	GHz	—	-2.7	—	3.1	
Output Power	dBm	2.7 GHz	—	57.0	—	
		2.9 GHz	—	57.9	—	
		3.1 GHz	—	57.0	—	
Drain Efficiency	%	2.7 GHz	—	63	—	
		2.9 GHz	—	71	—	P_{IN} = 46 dBm
		3.1 GHz	—	61	—	
LSG	dB	2.7 GHz	—	11.0	—	
		2.9 GHz	—	11.9	—	
		3.1 GHz	—	11.0	—	
Small-Signal		—	—	14.5	—	
Input Return		—	—	-15	—	P_{IN} = -20 dBm
Output Return		—	—	-6	—	

Large Signal Performance Versus Temperature – Short Pulse

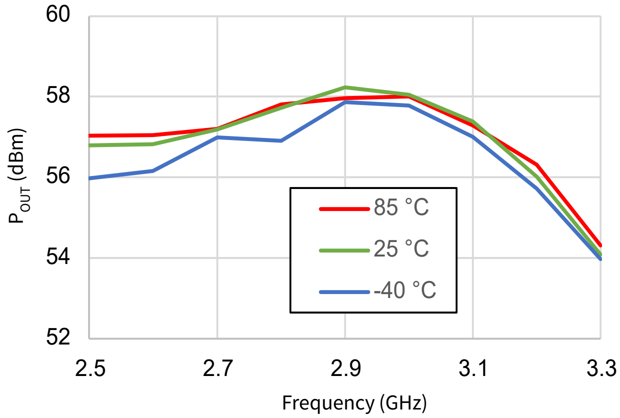


Figure 2. P_{OUT} v. Frequency v. Temperature

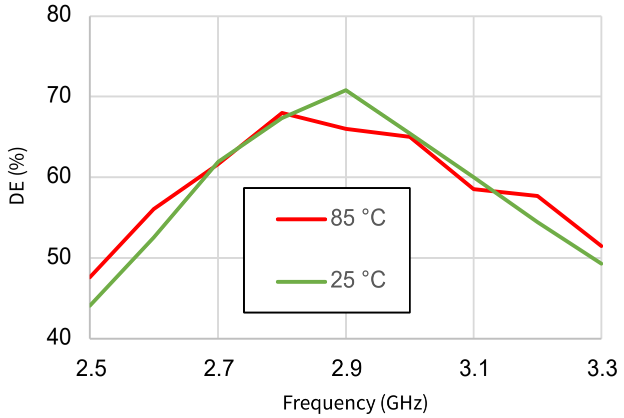


Figure 3. DE v. Frequency v. Temperature

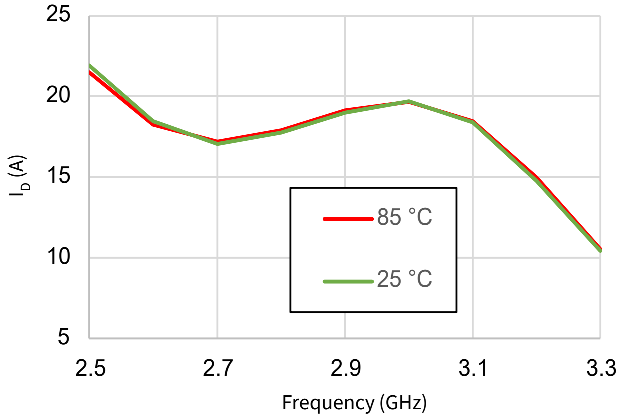


Figure 4. I_D v. Frequency v. Temperature

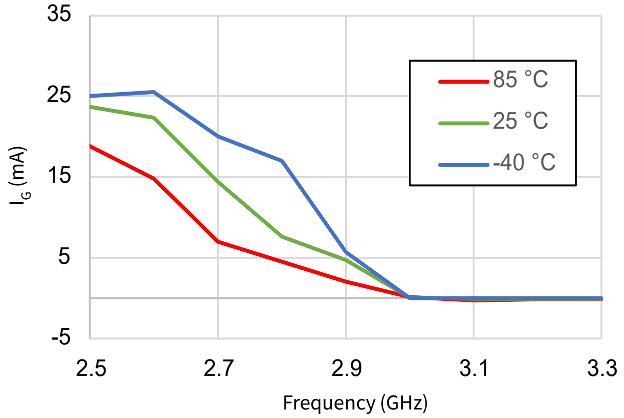


Figure 5. I_G v. Frequency v. Temperature

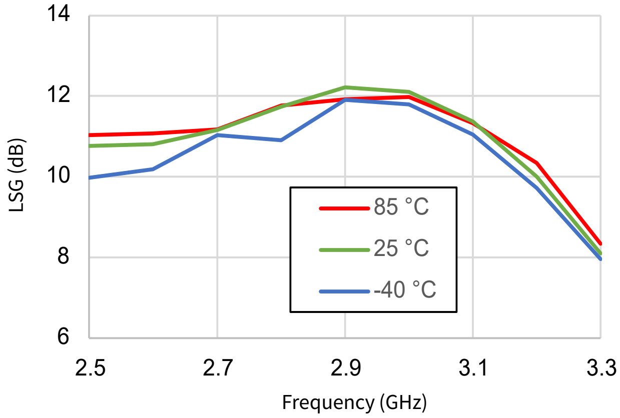


Figure 6. LSG v. Frequency v. Temperature

Large Signal Performance Versus V_D – Short Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 100µs, DC = 10%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

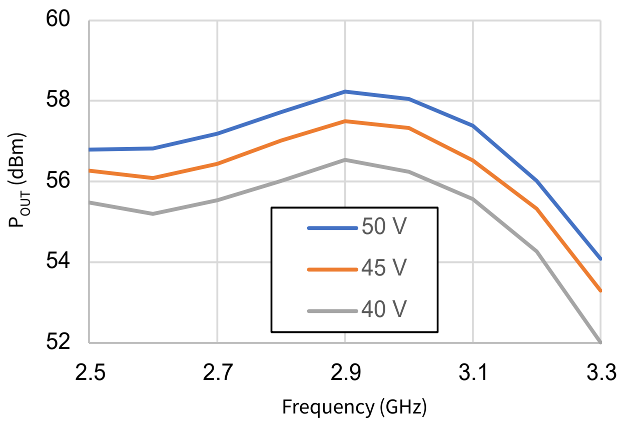


Figure 7. P_{OUT} v. Frequency v. V_D

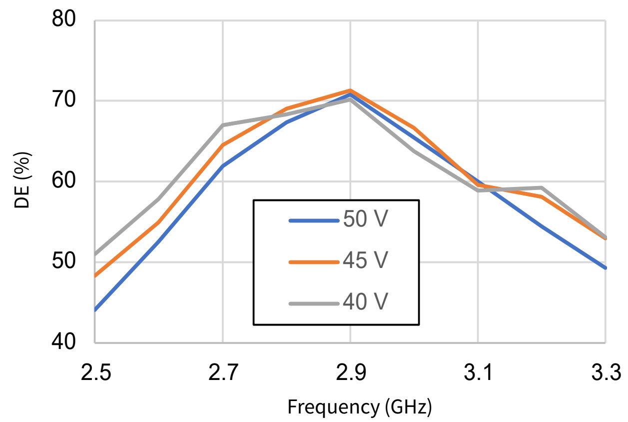


Figure 8. DE v. Frequency v. V_D

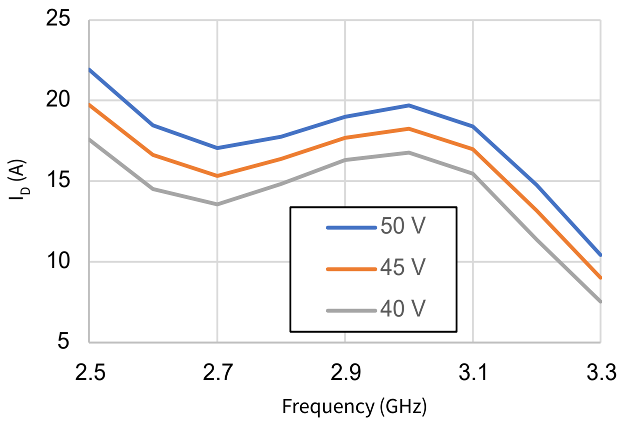


Figure 9. I_D v. Frequency v. V_D

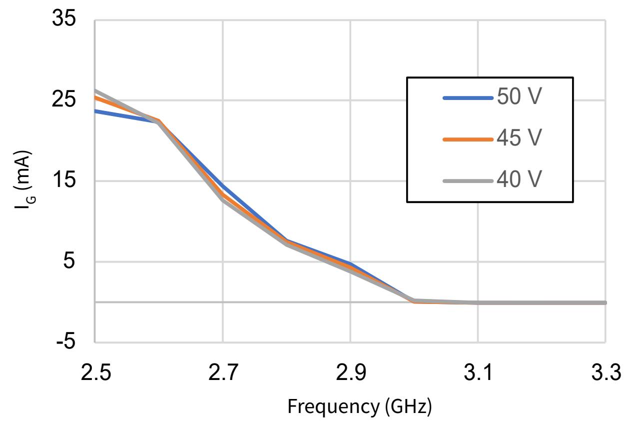


Figure 10. I_G v. Frequency v. V_D

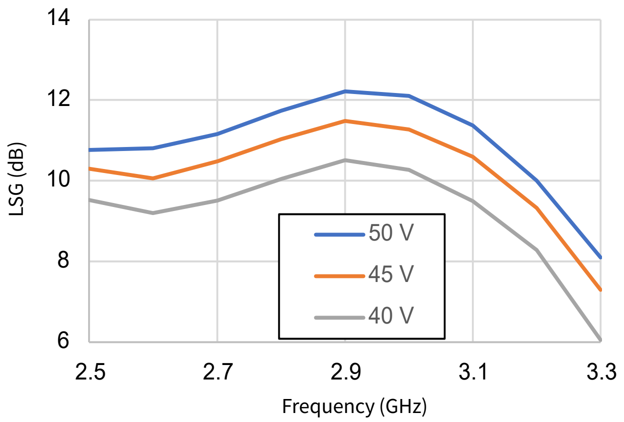


Figure 11. LSG v. Frequency v. V_D

Large Signal Performance Versus V_D – Short Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 100µs, DC = 10%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

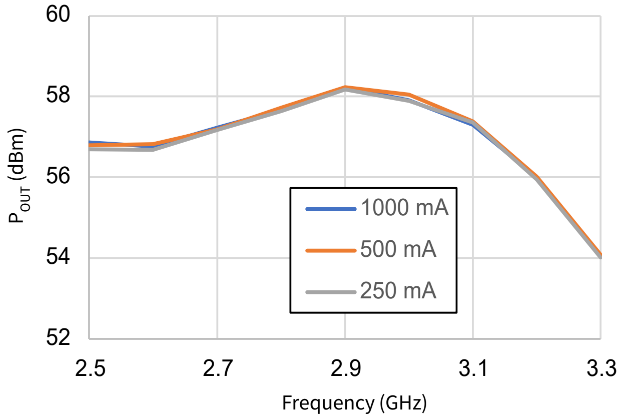


Figure 12. P_{OUT} v. Frequency v. I_{DQ}

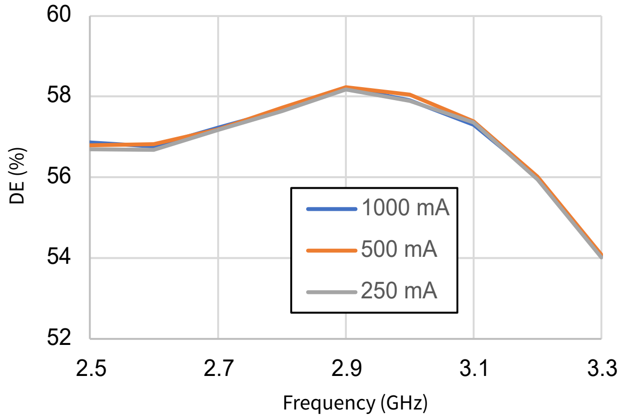


Figure 13. DE v. Frequency v. I_{DQ}

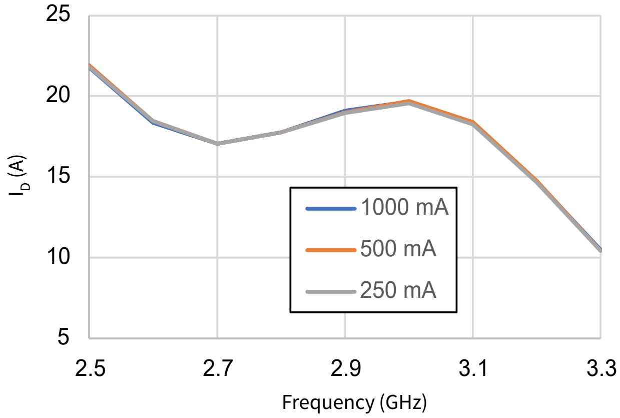


Figure 14. I_D v. Frequency v. I_{DQ}

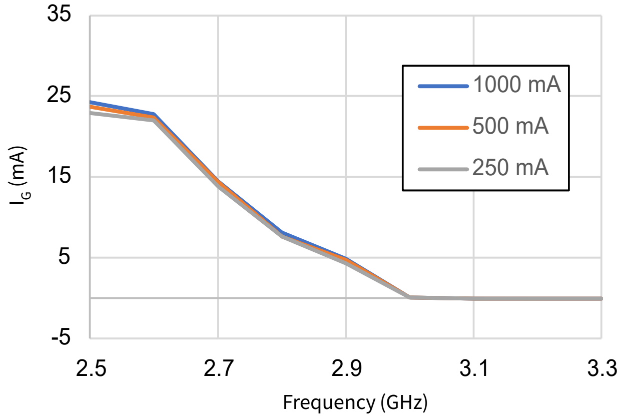


Figure 15. I_G v. Frequency v. I_{DQ}

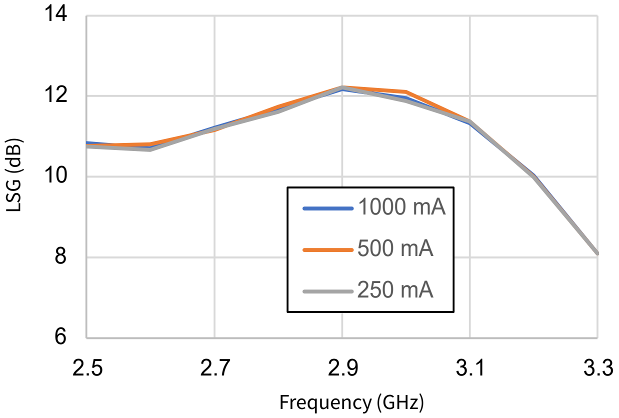


Figure 16. LSG v. Frequency v. I_{DQ}

Drive-up Versus Frequency – Short Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 100µs, DC = 10%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

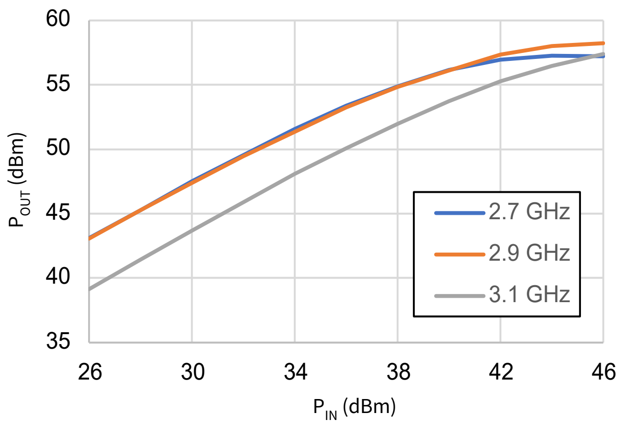


Figure 17. P_{OUT} v. P_{IN} v. Frequency

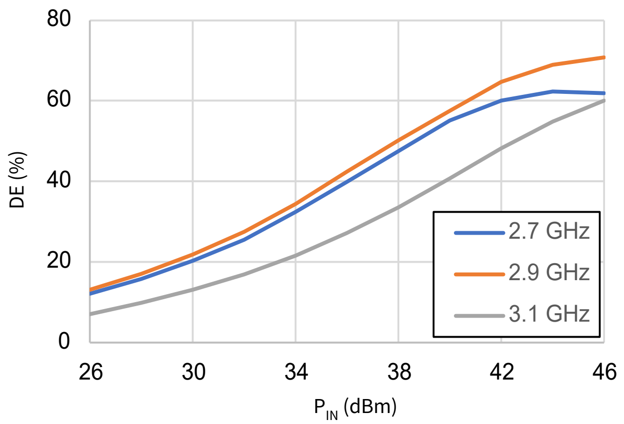


Figure 18. DE v. P_{IN} v. Frequency

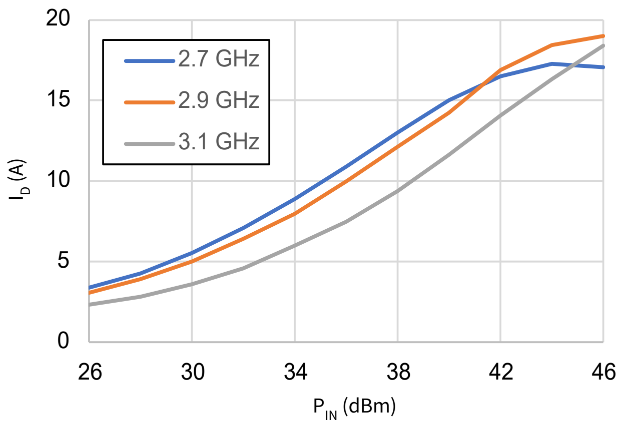


Figure 19. I_D v. P_{IN} v. Frequency

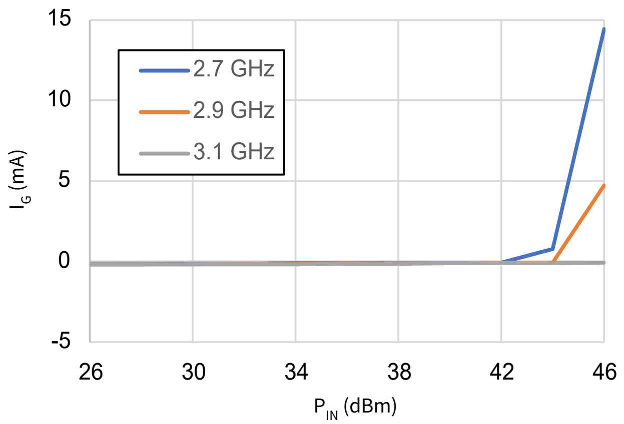


Figure 20. I_G v. P_{IN} v. Frequency

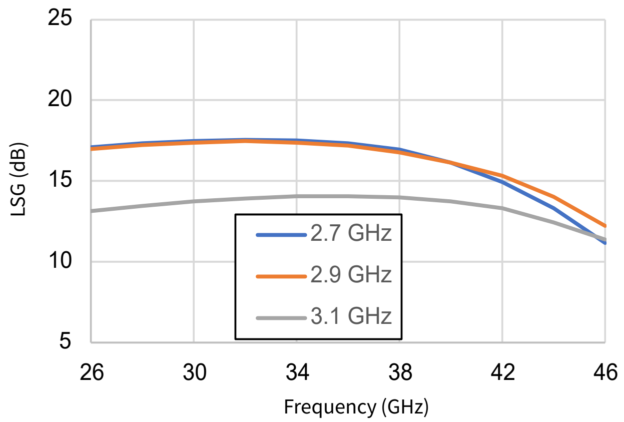


Figure 21. Gain v. P_{IN} v. Frequency

Drive-up Versus Temperature – Short Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 100µs, DC = 10%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

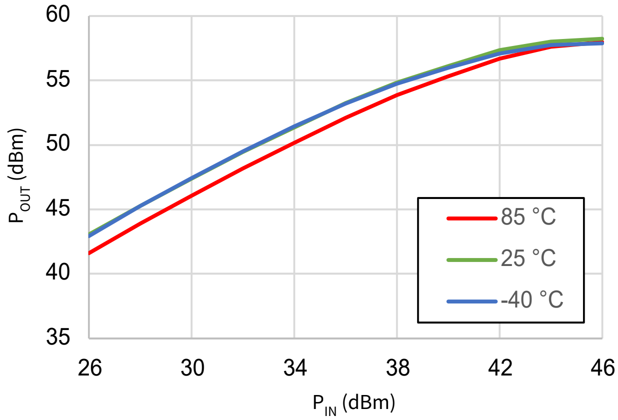


Figure 22. P_{OUT} v. P_{IN} v. Temperature

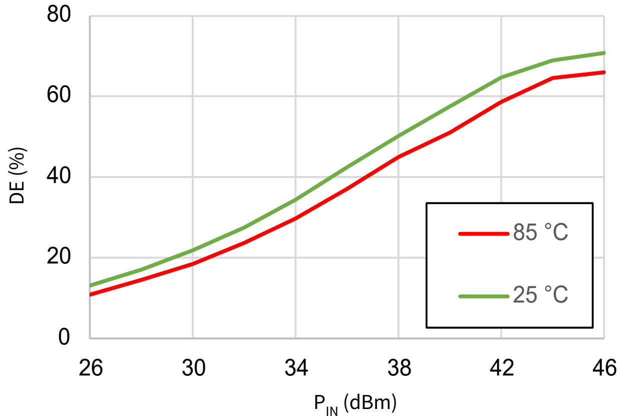


Figure 23. DE v. P_{IN} v. Temperature

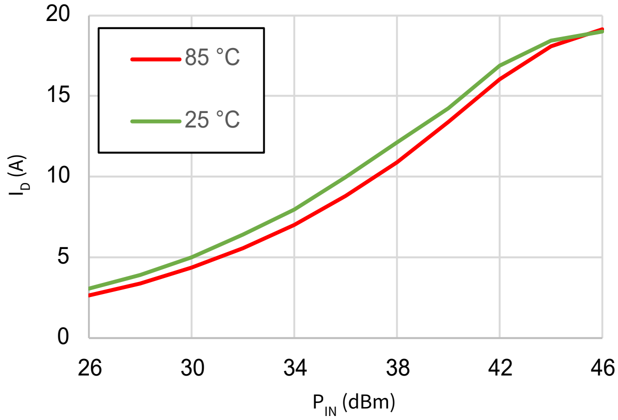


Figure 24. I_D v. P_{IN} v. Temperature

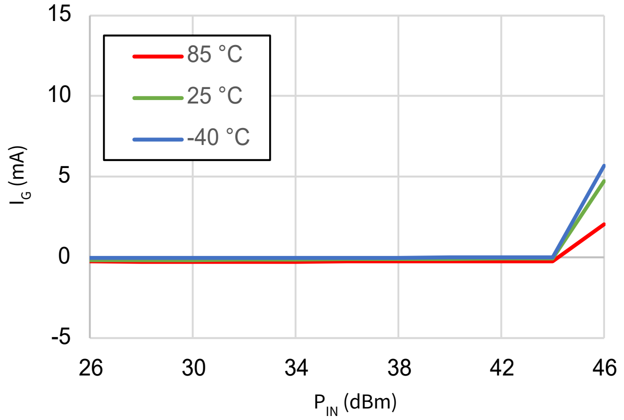


Figure 25. I_G v. P_{IN} v. Temperature

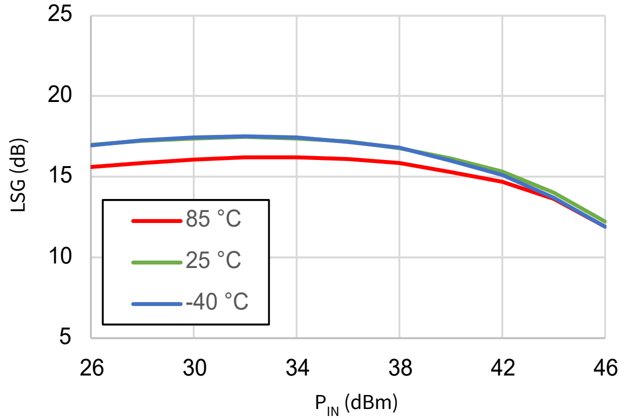


Figure 26. Gain v. P_{IN} v. Temperature

Drive-up Versus V_D – Short Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 100µs, DC = 10%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

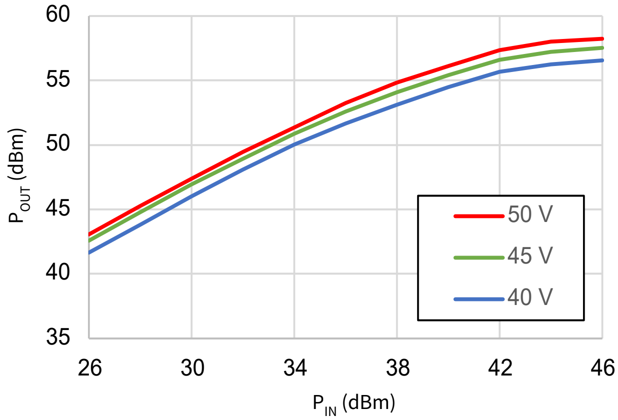


Figure 27. P_{OUT} v. P_{IN} v. V_D

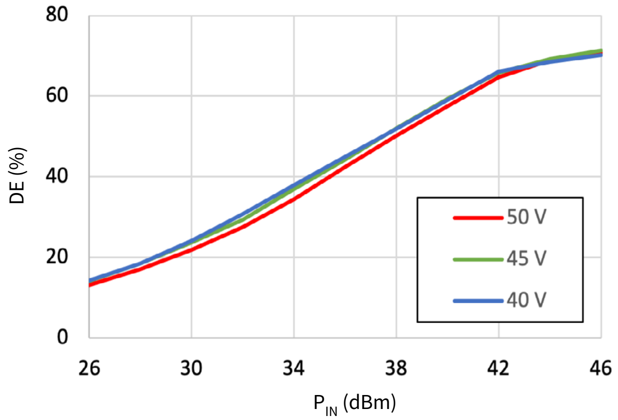


Figure 28. DE v. P_{IN} v. V_D

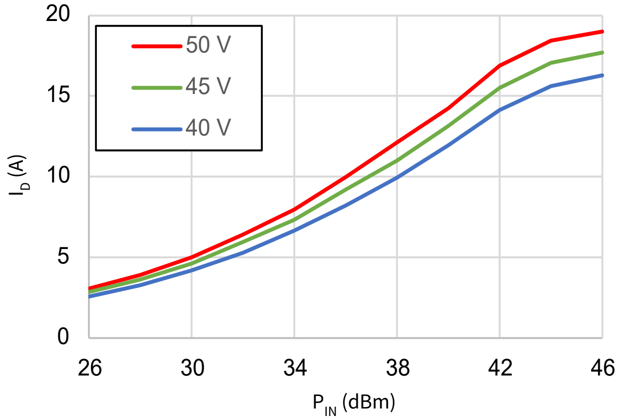


Figure 29. I_D v. P_{IN} v. V_D

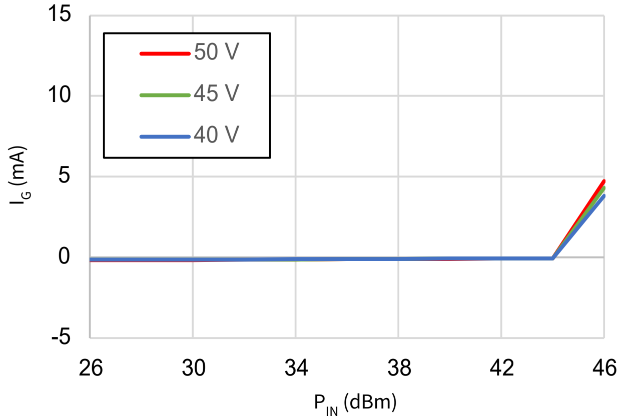


Figure 30. I_G v. P_{IN} v. V_D

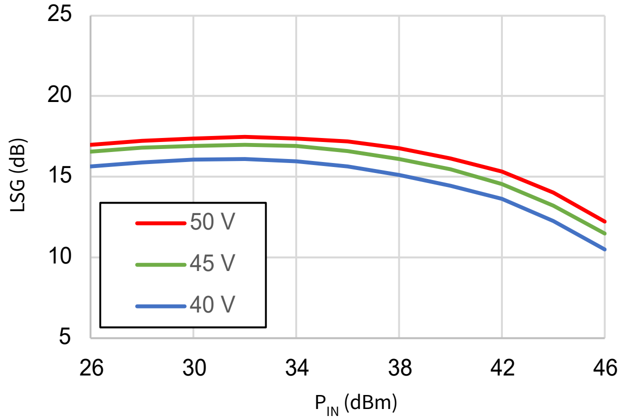


Figure 31. Gain v. P_{IN} v. V_D

Drive up Versus I_{DQ} – Short Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 100µs, DC = 10%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

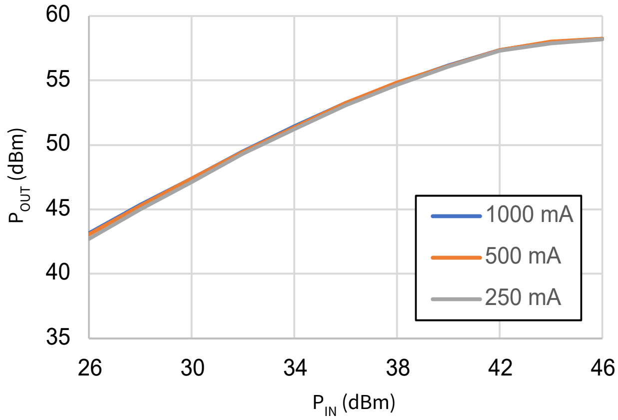


Figure 32. P_{OUT} v. P_{IN} v. I_{DQ}

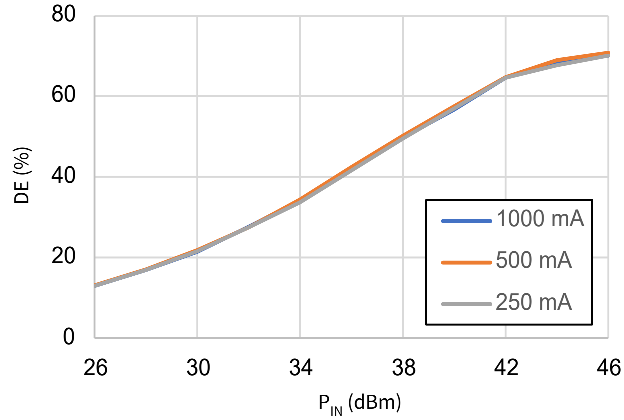


Figure 33. DE v. P_{IN} v. I_{DQ}

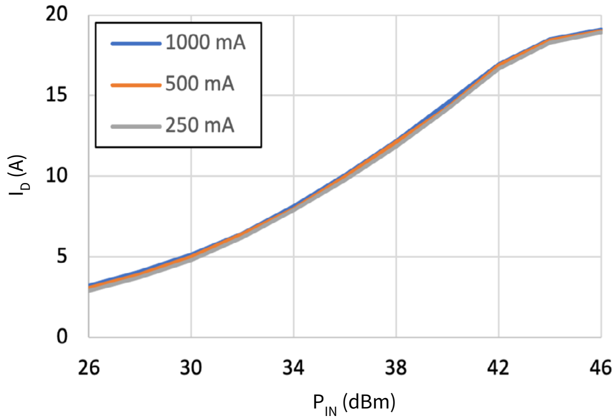


Figure 34. I_D v. P_{IN} v. I_{DQ}

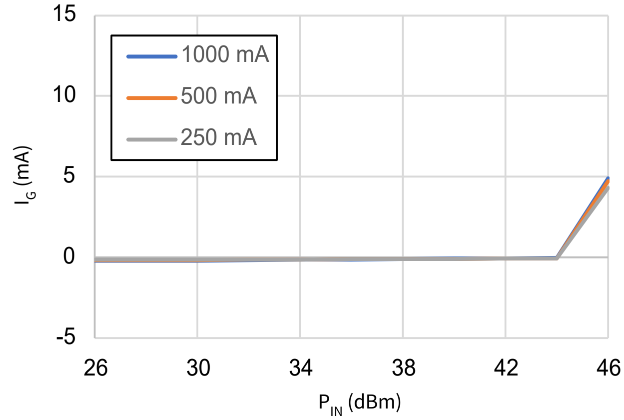


Figure 35. I_G v. P_{IN} v. I_{DQ}

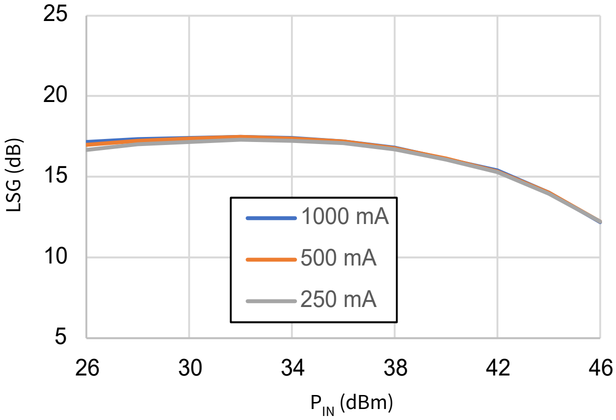


Figure 36. Gain v. P_{IN} v. I_{DQ}

Large Signal Performance Versus Temperature – Short Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 100µs, DC = 10%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

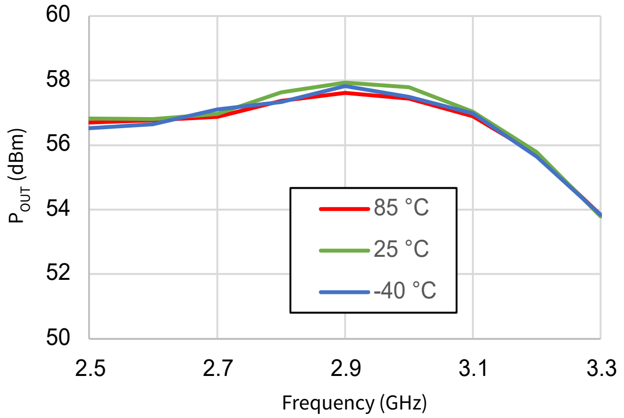


Figure 37. P_{OUT} v. Frequency v. Temperature

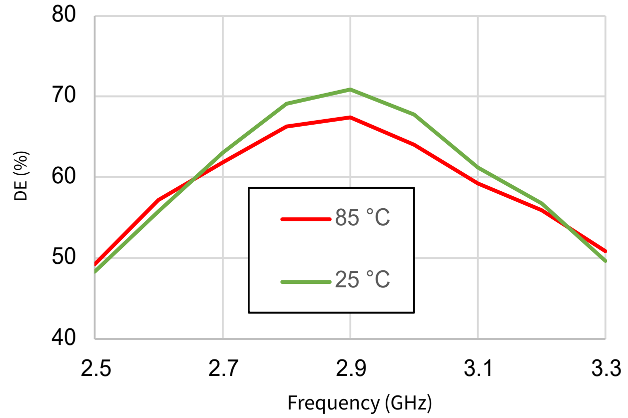


Figure 38. DE v. Frequency v. Temperature

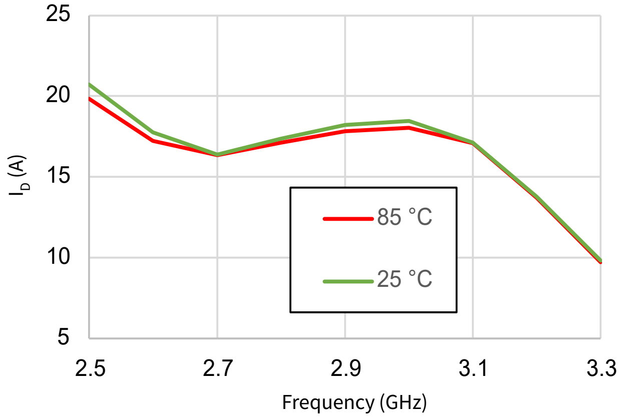


Figure 39. I_D v. Frequency v. Temperature

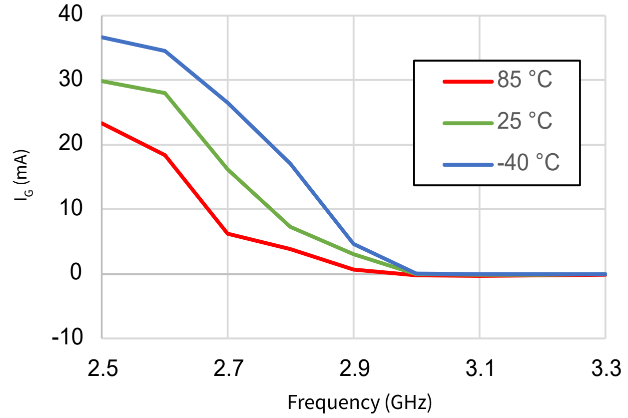


Figure 40. I_G v. Frequency v. Temperature

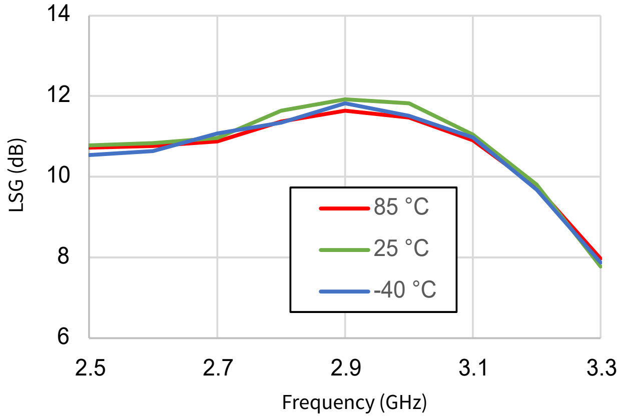


Figure 41. LSG v. Frequency v. Temperature

Large Signal Performance Versus V_D – Short Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 100µs, DC = 10%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

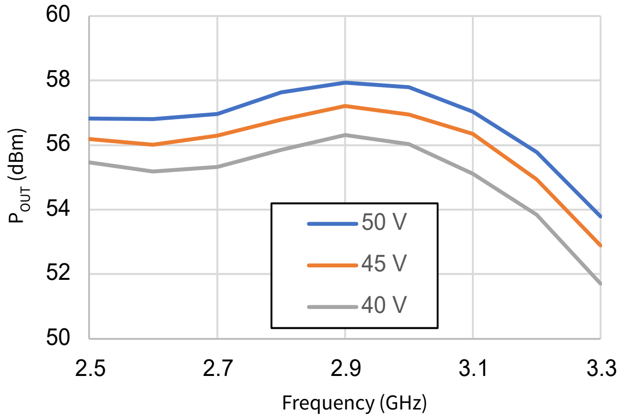


Figure 42. P_{OUT} v. Frequency v. V_D

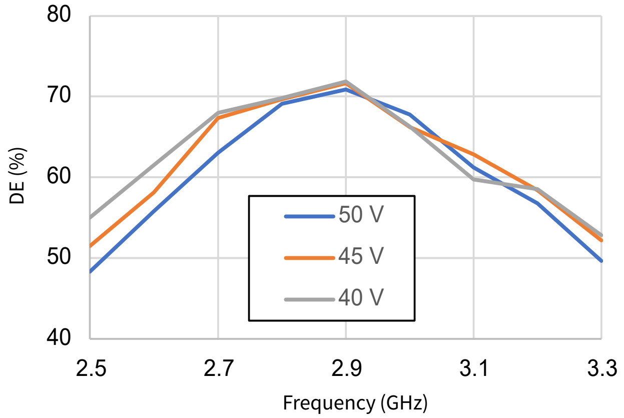


Figure 43. DE v. Frequency v. V_D

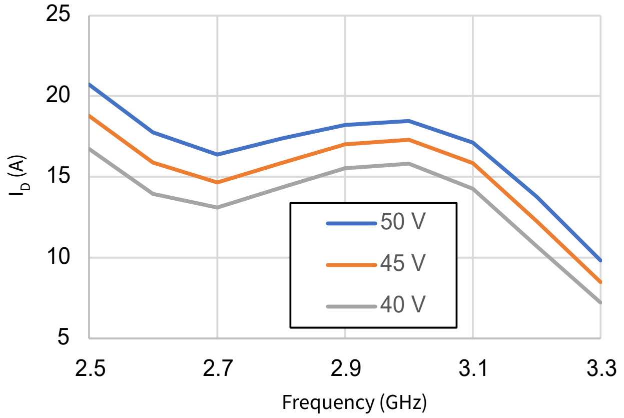


Figure 44. I_D v. Frequency v. V_D

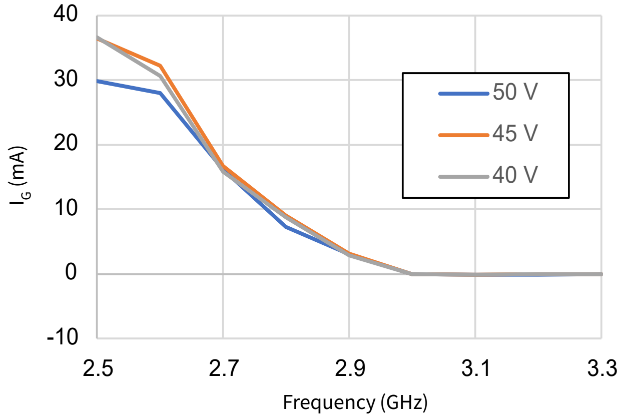


Figure 45. I_G v. Frequency v. V_D

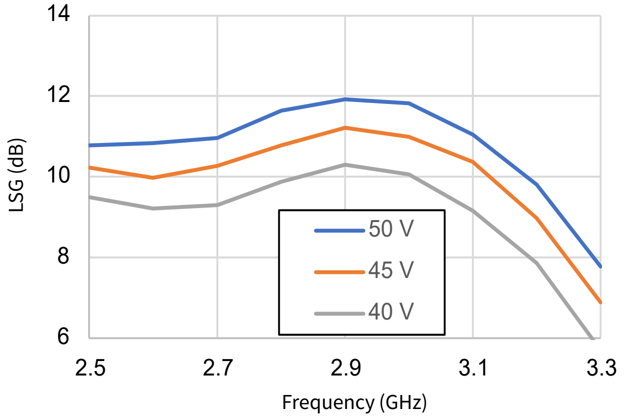


Figure 46. LSG v. Frequency v. V_D

Large Signal Performance Versus I_{DQ} – Short Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 100µs, DC = 10%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

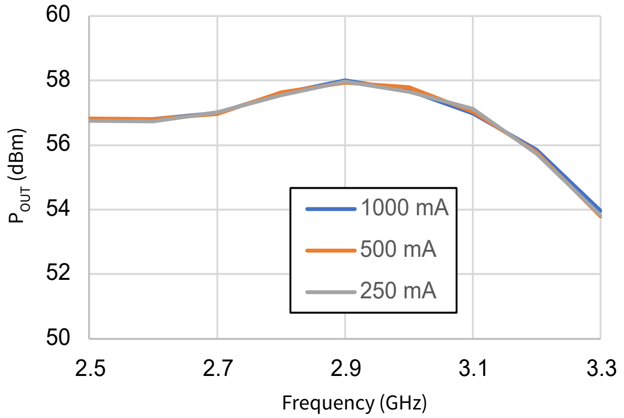


Figure 47. P_{OUT} v. Frequency v. I_{DQ}

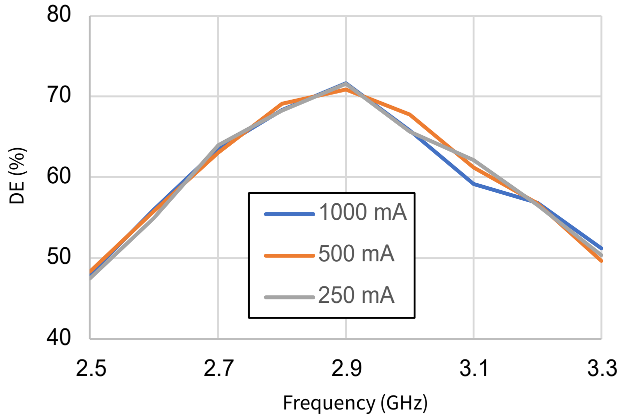


Figure 48. DE v. Frequency v. I_{DQ}

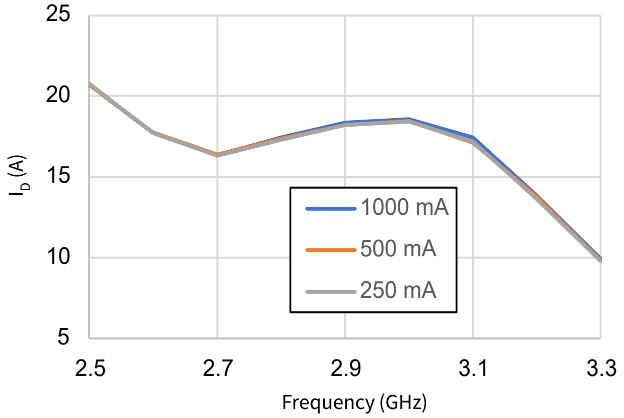


Figure 49. I_D v. Frequency v. I_{DQ}

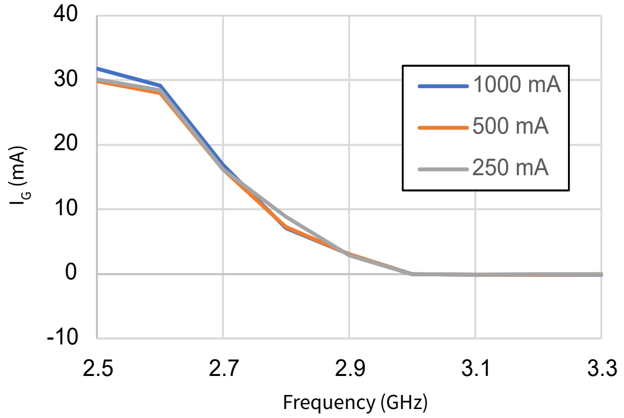


Figure 50. I_G v. Frequency v. I_{DQ}

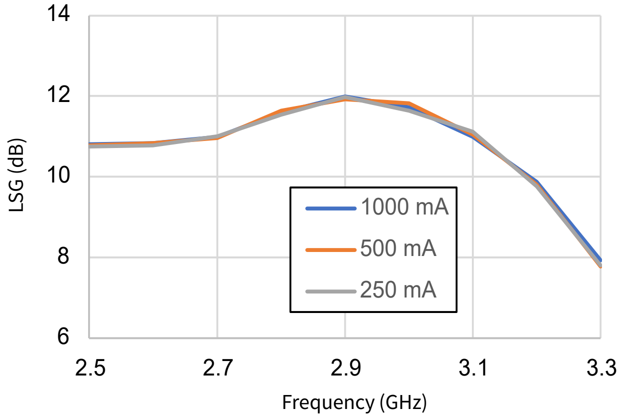


Figure 51. LSG v. Frequency v. I_{DQ}

Drive-up Versus Frequency – Short Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 100µs, DC = 10%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

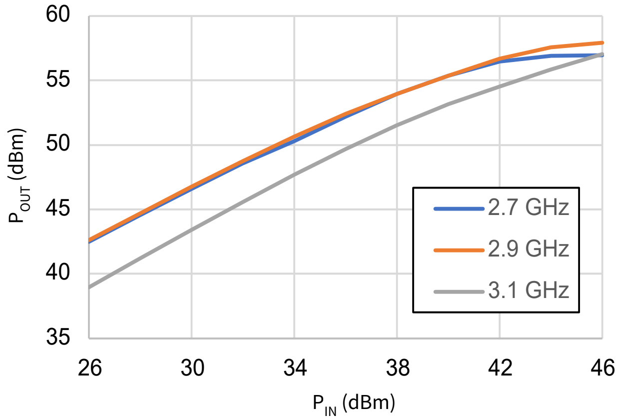


Figure 52. P_{OUT} v. P_{IN} v. Frequency

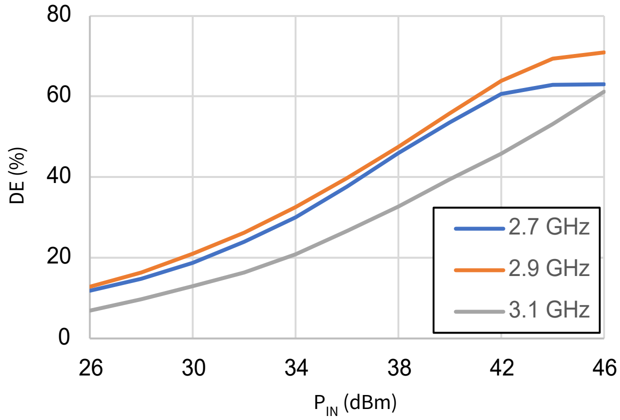


Figure 53. DE v. P_{IN} v. Frequency

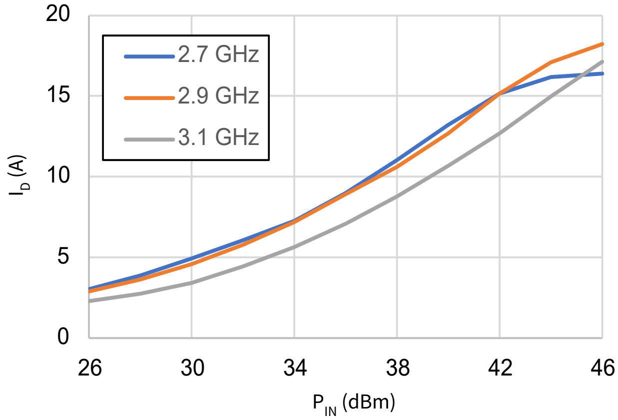


Figure 54. I_D v. P_{IN} v. Frequency

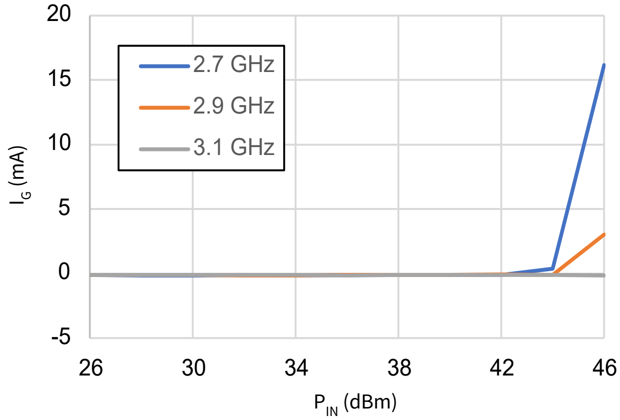


Figure 55. I_G v. P_{IN} v. Frequency

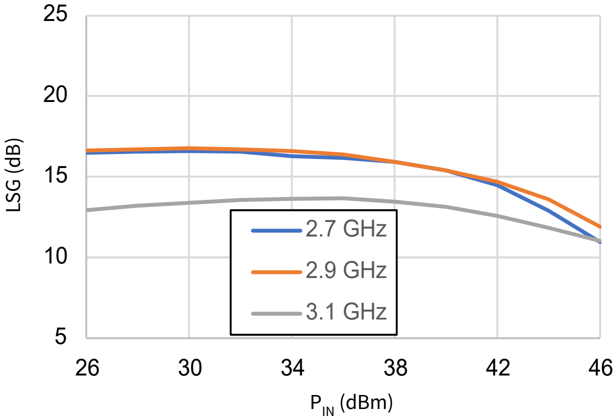


Figure 56. Gain v. P_{IN} v. Frequency

Drive-up Versus Temperature – Short Pulse

Test conditions unless otherwise noted: $V_D = 50$ V, $I_{DQ} = 500$ mA, PW = 100µs, DC = 10%, $P_{IN} = 46$ dBm, $T_{BASE} = 25°C$, Frequency = 2.9 GHz

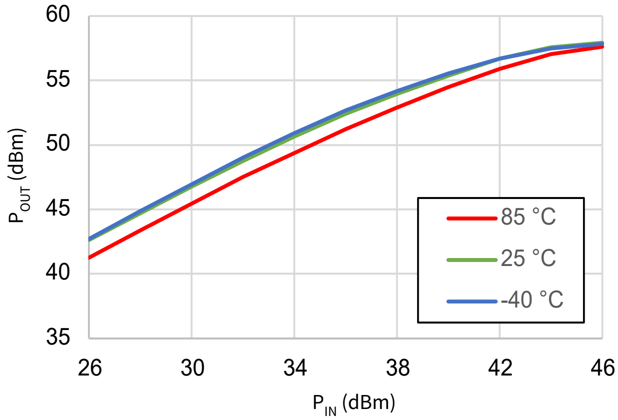


Figure 57. P_{OUT} v. P_{IN} v. Temperature

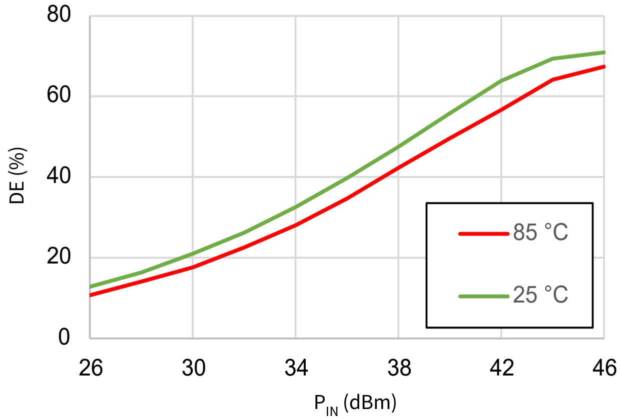


Figure 58. DE v. P_{IN} v. Temperature

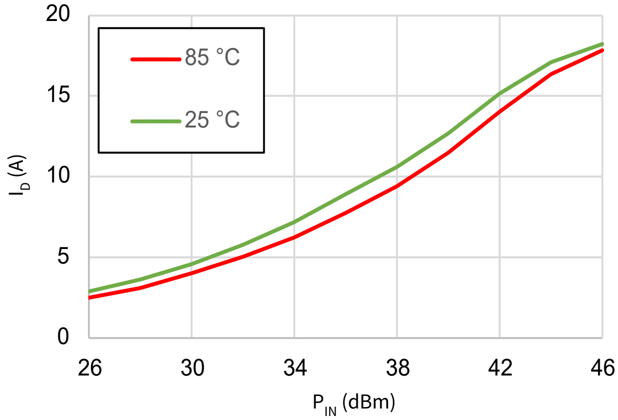


Figure 59. I_D v. P_{IN} v. Temperature

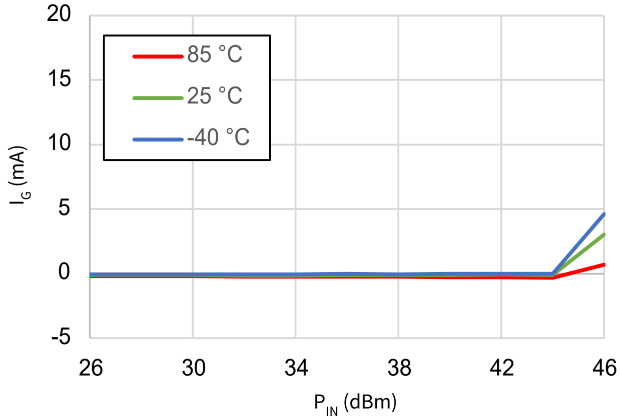


Figure 60. I_G v. P_{IN} v. Temperature

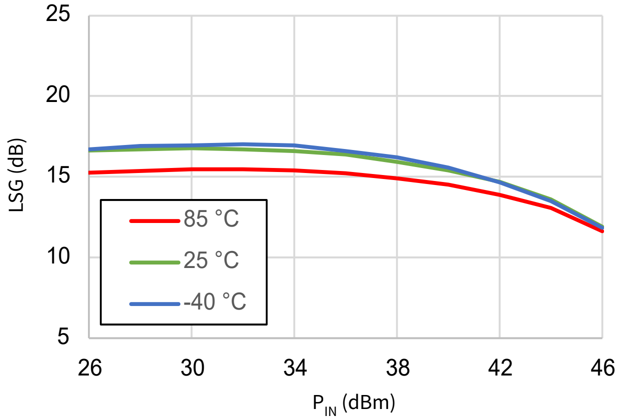


Figure 61. Gain v. P_{IN} v. Temperature

Drive-up Versus V_D – Long Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 2000µs, DC = 20%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

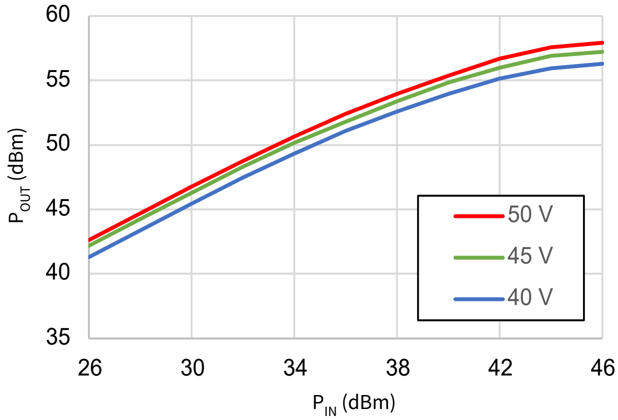


Figure 62. P_{OUT} v. P_{IN} v. V_D

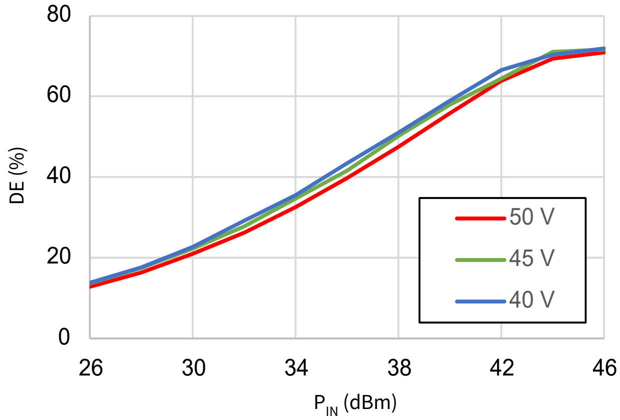


Figure 63. DE v. P_{IN} v. V_D

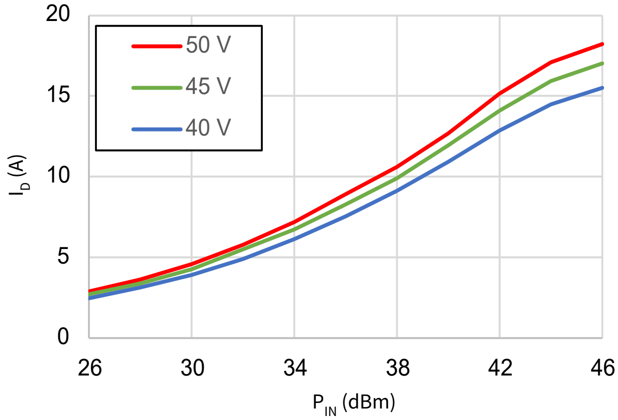


Figure 64. I_D v. P_{IN} v. V_D

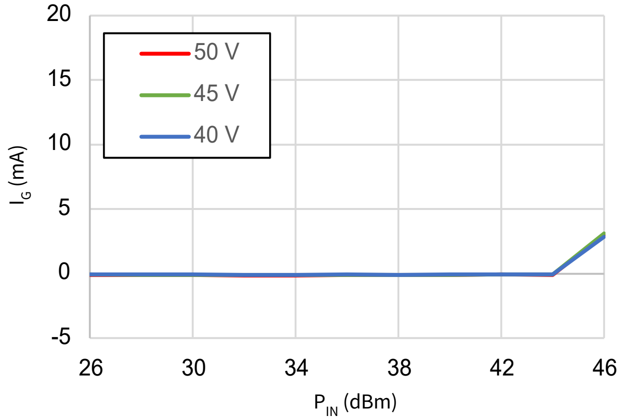


Figure 65. I_G v. P_{IN} v. V_D

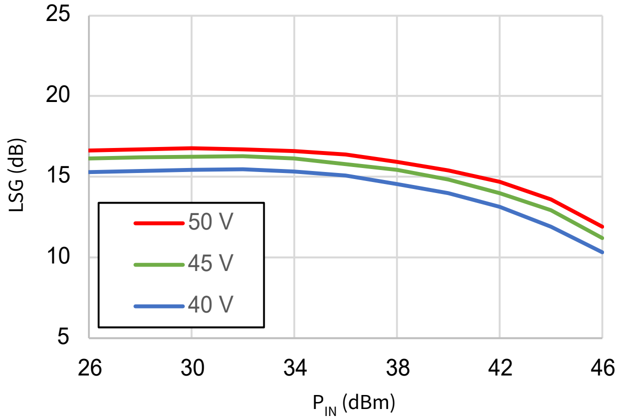


Figure 66. Gain v. P_{IN} v. V_D

Drive-up Versus V_D – Long Pulse

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, PW = 2000µs, DC = 20%, P_{IN} = 46 dBm, T_{BASE} = 25°C, Frequency = 2.9 GHz

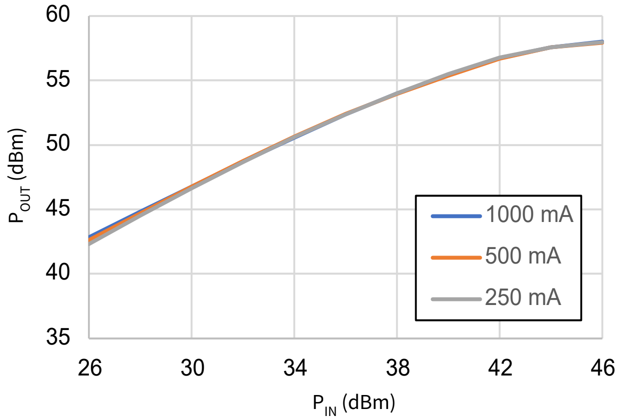


Figure 67. P_{OUT} v. P_{IN} v. I_{DQ}

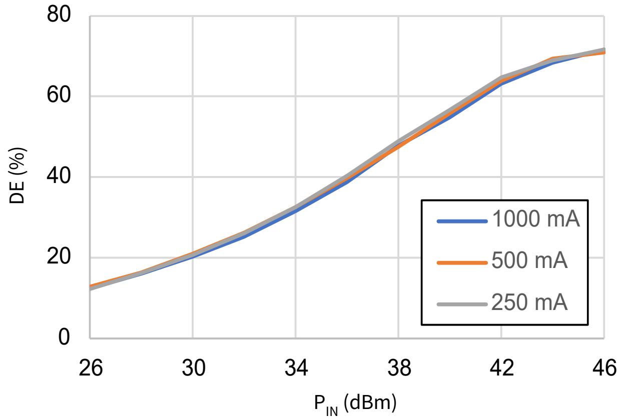


Figure 68. DE v. P_{IN} v. I_{DQ}

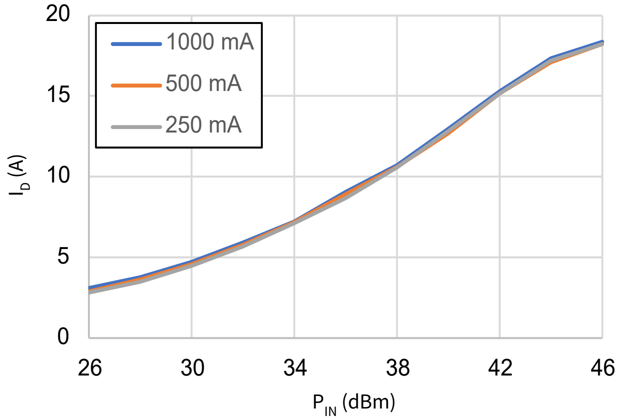


Figure 69. I_D v. P_{IN} v. I_{DQ}

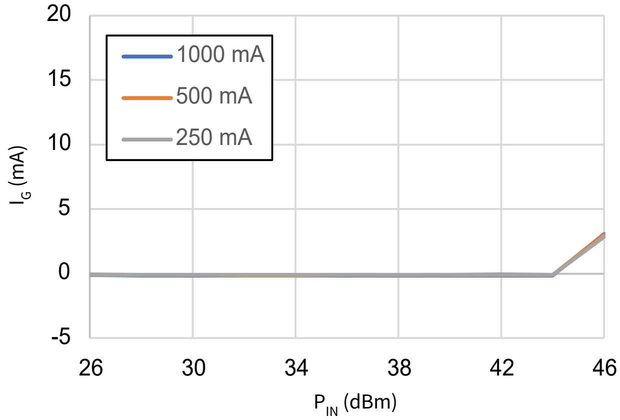


Figure 70. I_G v. P_{IN} v. I_{DQ}

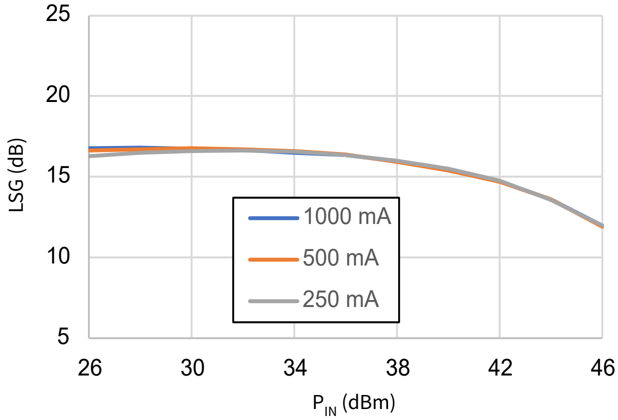


Figure 71. Gain v. P_{IN} v. I_{DQ}

Small Signal v. Temperature and Bias

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500 mA, P_{IN} = -20 dBm, T_{BASE} = 25°C

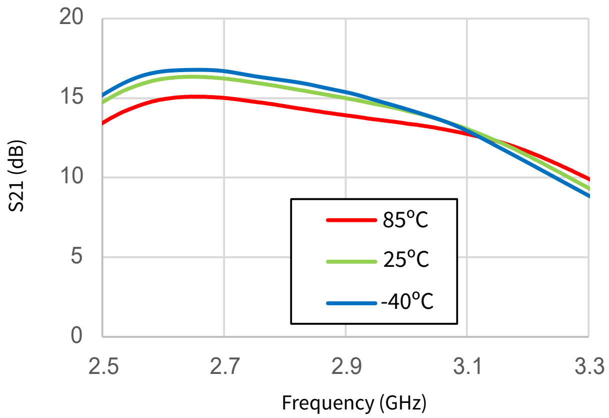


Figure 72. S21 v. Frequency v. Temperature

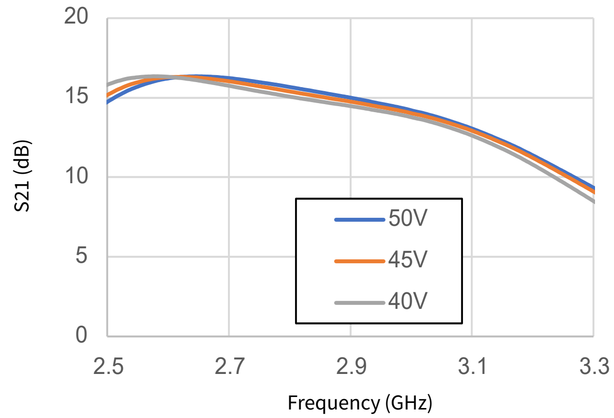


Figure 73. S21 v. Frequency v. V_D

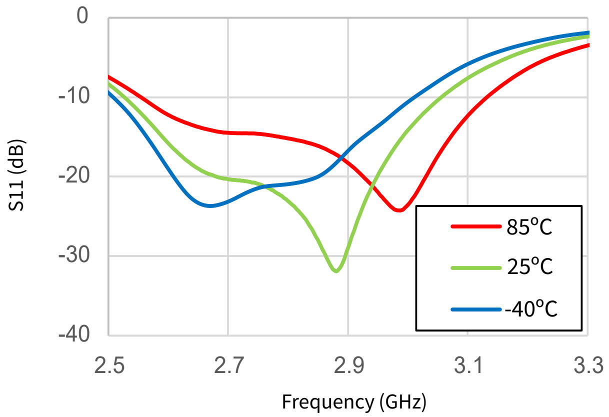


Figure 74. S11 v. Frequency v. Temperature

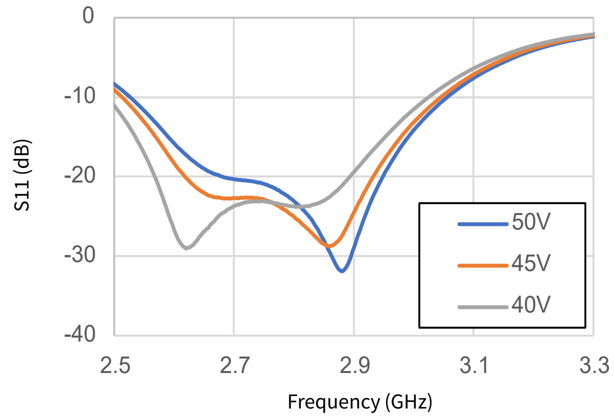


Figure 75. S11 v. Frequency v. V_D

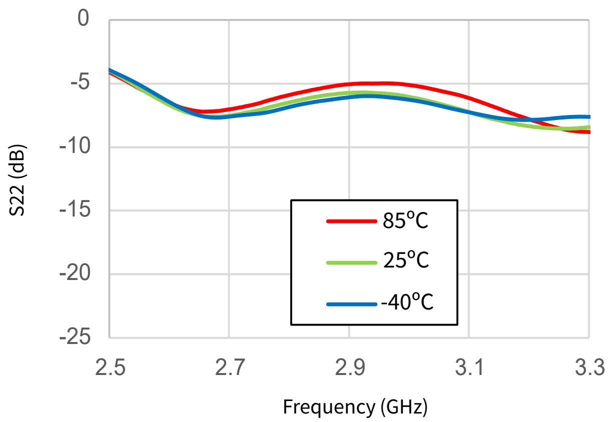


Figure 76. S22 v. Frequency v. Temperature

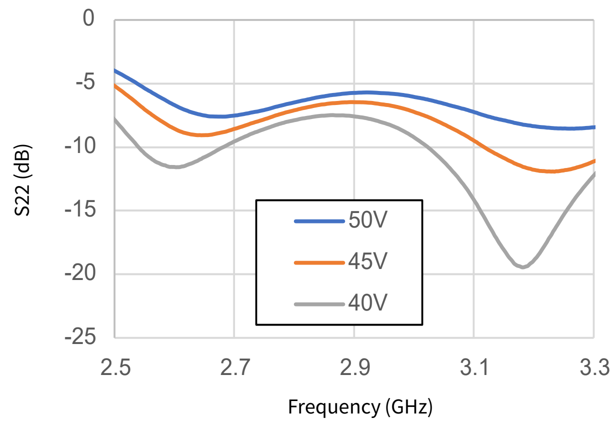


Figure 77. S22 v. Frequency v. V_D

Small Signal v. Bias

Test conditions unless otherwise noted: $V_D = 50$ V, $I_{DQ} = 500$ mA, $P_{IN} = -20$ dBm, $T_{BASE} = 25^{\circ}$C

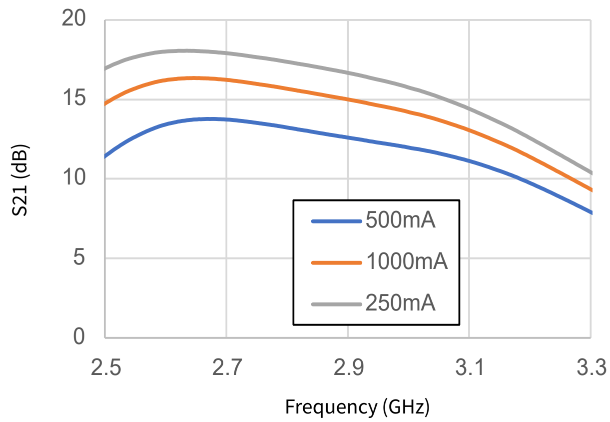


Figure 78. S21 v. Frequency v. I_{DQ}

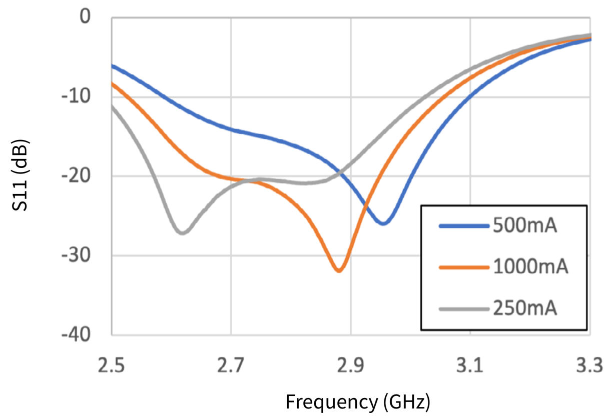


Figure 79. S11 v. Frequency v. I_{DQ}

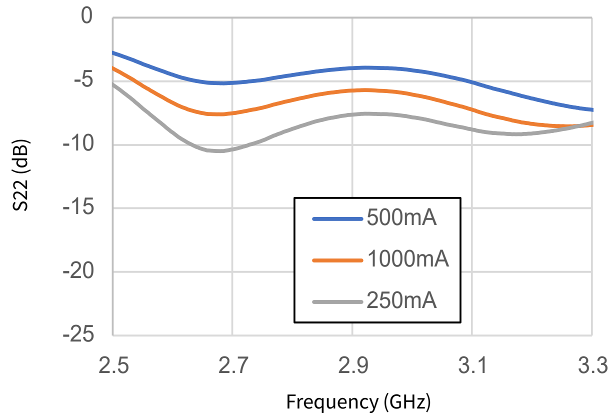


Figure 80. S22 v. Frequency v. I_{DQ}

Harmonics

Test conditions unless otherwise noted: V_D = 50 V, I_{DQ} = 500mA, PW = 2000µs, DC = 20%, P_{IN} = 46dBm, Frequency 1= 2.7 GHz (F1), Frequency 2 = 2.9 GHz (F2), Frequency 3 = 3.1 GHz (F3), T_{BASE} = 25°C

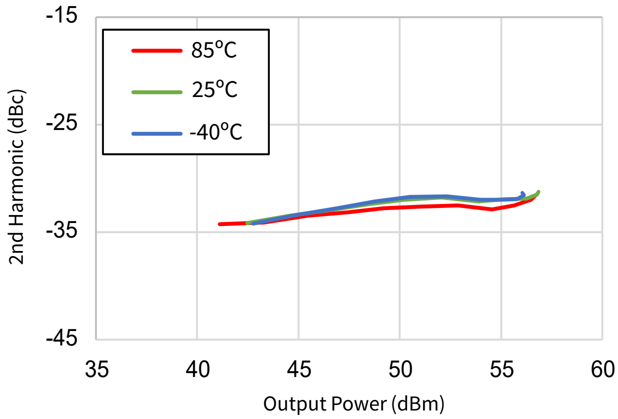


Figure 81. 2f v. P_{OUT} v. Temperature, F1

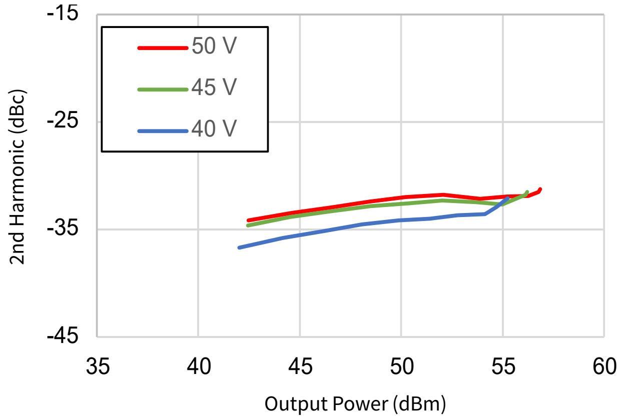


Figure 82. 2f v. P_{OUT} v. V_D, F1

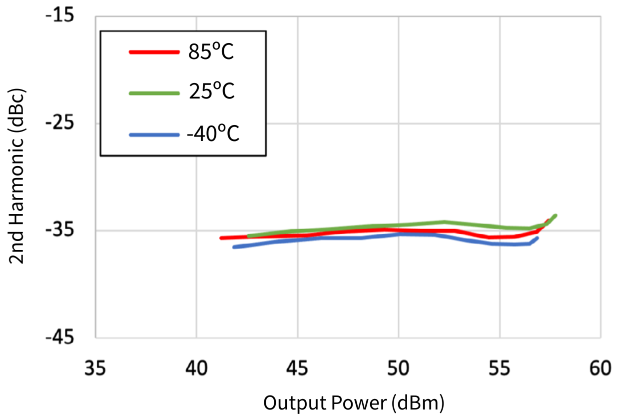


Figure 83. 2f v. P_{OUT} v. Temperature, F2

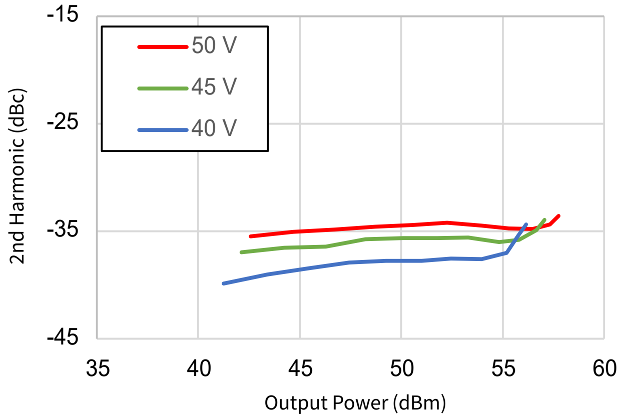


Figure 84. 2f v. P_{OUT} v. V_D, F2

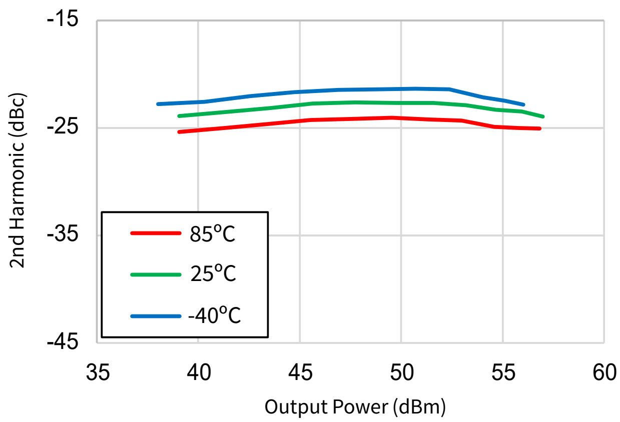


Figure 85. 2f v. P_{OUT} v. Temperature, F3

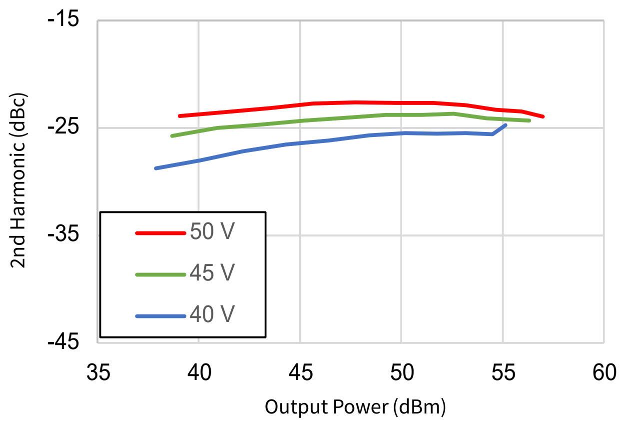
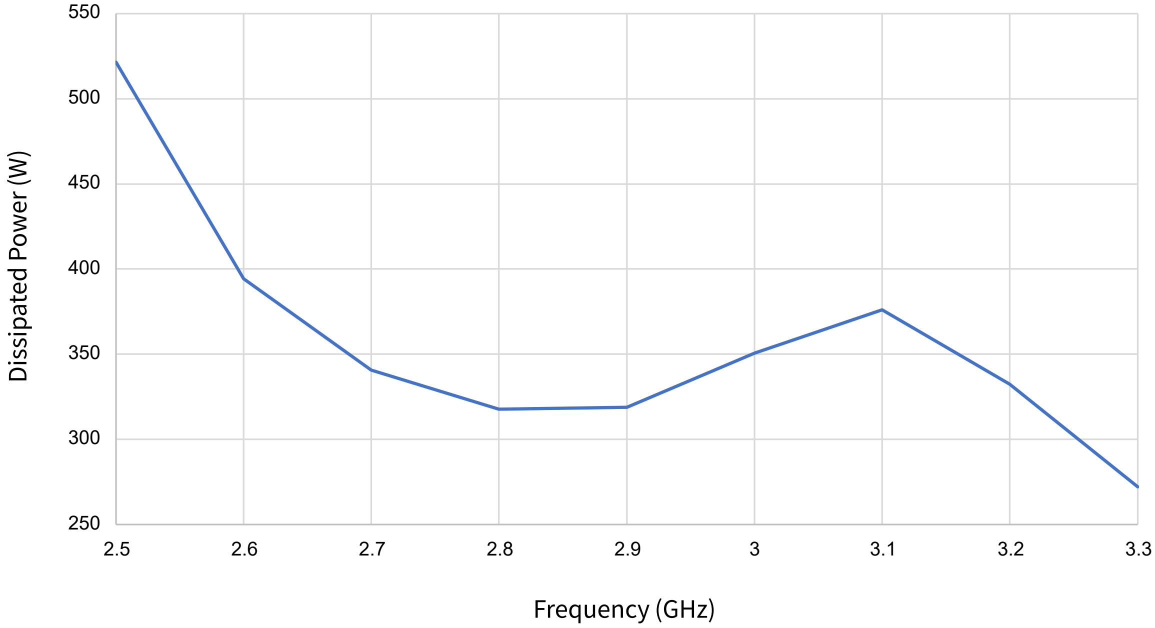


Figure 86. 2f v. P_{OUT} v. V_D, F3

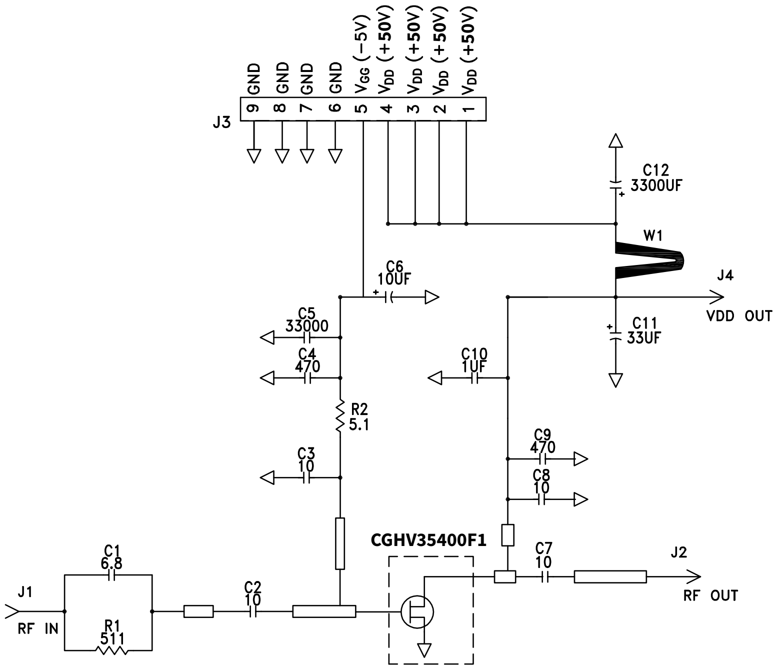
Thermal Information

Thermal Characteristics	Symbol	Value	Operating Conditions
Operating Junction Temperature	T_J	212	Freq = 2.9 GHz, V_D = 50 V, I_{DQ} = 500 mA, I_{DRIVE} = 18.2 A , P_{IN} = 46 dBm, P_{OUT} = 57.9 dBm, P_{DISS} = 319 W, T_{CASE} = 85°C, PW = 2000 µs, DC = 20%
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.4	

Power Dissipation v. Frequency (T_{CASE} = 85°C)



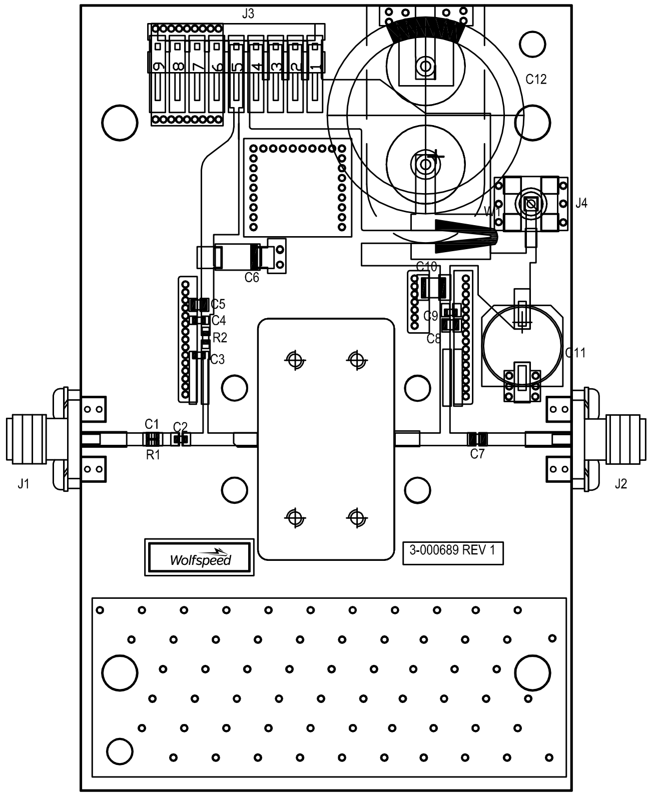
CGHV31500F1-AMP Evaluation Board Schematic



CGHV31500F1-AMP Bill of Materials

Designator	Description	Qty
R1	RES, 511 ohm, +/- 1%, 1/16W, 0603	1
R2	RES, 5.1 ohm, +/- 1%, 1/16W, 0603	1
C1	CAP, 6.8 pF, +/-0.25%, 250V, 0603	1
C2, C7, C8	CAP, 10.0 pF, +/-1%, 250V, 0805	3
C3	CAP, 10.0 pF, +/-5%, 250V, 0603	1
C4, C9	CAP, 470 pF, 5%, 100V, 0603, X	2
C5	CAP, 33000 pF, 0805, 100V, X7R	1
C6	CAP, 10 µF 16V TANTALUM	1
C10	CAP, 1.0 µF, 100V, 10%, X7R, 1210	1
C11	CAP, 33 µF, 20%, G CASE	1
C12	CAP, 3300 µF, +/-20%, 100V, ELECTROLYTIC	1
J1, J2	CONN, SMA, PANEL MOUNT JACK, FL	2
J3	HEADER, RT>PLZ, 0.1CEN LK 9POS	1
J4	CONNECTOR; SMB, Straight, JACK, SMD	1
W1	CABLE, 18 AWG, 4.2	1
	PCB, RO4350, 2.5 X 4.0 X 0.030	1
Q1	CGHV35400F1	1

CGHV31500F1-AMP Evaluation Board Assembly Drawing



Bias On Sequence

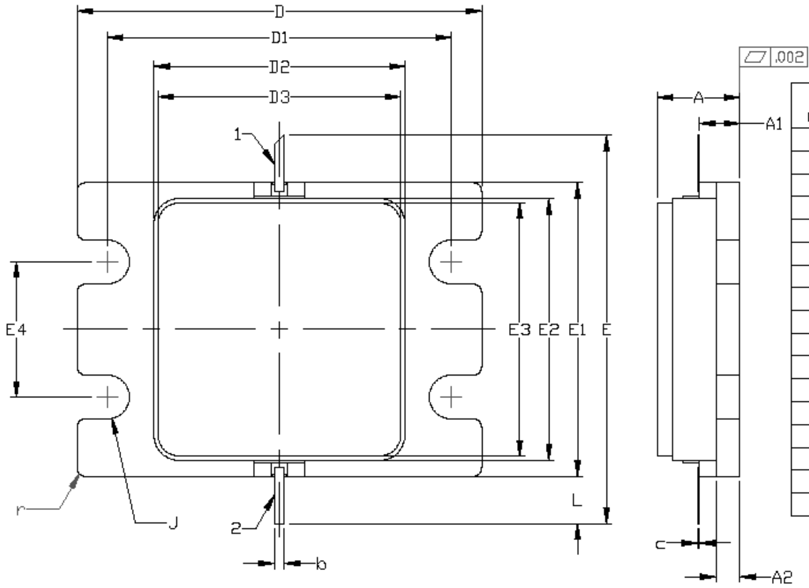
1. Ensure RF is turned-off
2. Apply pinch-off voltage of -5 V to the gate (V_G)
3. Apply nominal drain voltage (V_D)
4. Adjust Vg to obtain desired quiescent drain current (I_{DQ})
5. Apply RF

Bias Off Sequence

1. Turn RF off
2. Apply pinch-off to the gate (V_G=-5V)
3. Turn off drain voltage (V_D)
4. Turn off gate voltage (V_G)

Product Dimensions (Package 440226)

NOTES: (UNLESS OTHERWISE SPECIFIED)
1. INTERPRET DRAWING IN ACCORDANCE WITH ANSI Y14.5M-2009
2. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF .020 BEYOND EDGE OF LID
3. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF .008 IN ANY DIRECTION
4. ALL PLATED SURFACES ARE GOLD OVER NICKEL



DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX	NOTES
A	0.185	0.201	4.70	5.11	
A1	0.088	0.100	2.24	2.54	2x
A2	0.049	0.061	1.24	1.55	
b	0.022	0.026	0.56	0.66	2x
c	0.003	0.006	0.08	0.15	
D	0.935	0.955	23.75	24.26	
D1	0.797	0.809	20.24	20.55	2x
D2	0.581	0.593	14.76	15.06	
D3	0.565	0.571	14.35	14.50	
E	0.906		23.01		REF
E1	0.679	0.691	17.25	17.55	
E2	0.604	0.616	15.34	15.65	
E3	0.588	0.594	14.93	15.09	
E4	0.309	0.321	7.85	8.15	2x
J	ø0.097	ø0.107	ø2.46	ø2.72	4x
L	0.090	0.130	2.29	3.30	2x
r	0.02 TYP		0.51 TYP		12x

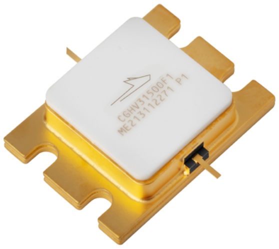
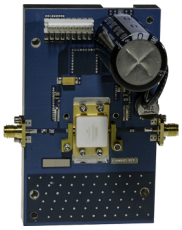
Pin	Description
1	GATE/RFIN
2	DRAIN/RFOUT
3	SOURCE/FLANGE

4600 Silicon Drive | Durham, NC 27703 | Tel: +1.919.313.5300

Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Classification Level	Test Methodology
Human Body Model	HBM	TBD	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 A114-D
Charge Device Model	CDM	TBD	ANSI/ESDA/JEDEC JS-002 Table 3	JEDEC JESD22 C101-C

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGHV35400F1	Packaged GaN HEMT	Each	
CGHV31500F1-AMP	Evaluation Board w/ GaN HEMT	Each	

For more information, please contact:

4600 Silicon Drive
Durham, NC 27703 USA
Tel: +1.919.313.5300
www.wolfspeed.com/RF

Sales Contact
RFSales@wolfspeed.com

RF Product Marketing Contact
RFMarketing@wolfspeed.com

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